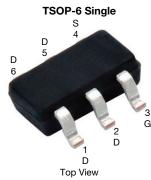
SQ3426CEV

www.vishay.com

Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

(3) G O

(1, 2, 5, 6) D



COMPLIANT HALOGEN

Marking Code: 9Hxxx

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.042			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.063			
I _D (A)	7			
Configuration	Single			

₅ = 4.5 V	0.063	(4) S N-Channel MOSFET
	Single	
INFORMATION		7005.0

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3426CEV (for detailed order number please see <u>www.vishay.com/doc?79771</u>)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		V _{DS}	60	V		
Gate-source voltage		V _{GS}	± 20	V		
Continuous drain current	T _C = 25 °C	1	7			
Continuous drain current	T _C = 125 °C	I _D	4			
Continuous source current (diode conduction)	I _S	6	А			
Pulsed drain current ^a		I _{DM}	29			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	10			
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	5	mJ		
Maximum neuror dissinction	T _C = 25 °C	P	5	W		
Maximum power dissipation	T _C = 125 °C	P _D	1.6	٧V		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction to ambient	PCB mount ^b	R _{thJA}	110	°C/W	
Junction to foot (drain)		R _{thJF}	30	0/10	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						•	•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = 250 μA		2	2.5	v	
	1	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	± 100	n A	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 300	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α	
		$V_{GS} = 10 V$	I _D = 5 A	-	0.034	0.042	1	
	Р	$V_{GS} = 10 V$	I _D = 5 A, T _J = 125 °C	-	-	0.073		
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 5 A, T _J = 175 °C	-	-	0.092	Ω	
		V _{GS} = 4.5 V	$I_D = 4 A$	-	0.037	0.063		
Forward transconductance a	g _{fs}	V _{DS} = 15 V, I _D = 4 A		-	21	-	S	
Dynamic ^b					•	•	•	
Input Capacitance	C _{iss}		V _{DS} = 30 V, f = 1 MHz	-	718	790	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	75	110		
Reverse Transfer Capacitance	C _{rss}			-	29	70		
Total Gate Charge ^c	Qg		V _{DS} = 30 V, I _D = 4 A	-	6.8	12	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 4.5 V		-	2.9	-		
Gate-Drain Charge ^c	Q _{gd}			-	2.0	-		
Gate Resistance	Rg		f = 1 MHz	1.9	3.1	5.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}		V _{DD} = 30 V, R _I = 7.5 Ω		9	14		
Rise Time ^c	tr	- V _{DD} =			3	18	- ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 4$ Å, $V_{GEN} = 10$ V, $R_g = 1 \Omega$		-	19	29		
Fall Time ^c	t _f			-	4	11		
Source-Drain Diode Ratings and Charact	eristics ^b							
Pulsed current ^a	I _{SM}			-	-	29	А	
Forward voltage	V _{SD}	I _F =	1.6 A, V _{GS} = 0 V	-	0.77	1.2	V	
Body diode reverse recovery time	t _{rr}			-	19	38	ns	
Body diode reverse recovery charge	Q _{rr}	1		-	18	36	nC	
Reverse recovery fall time	ta	$I_F = 4$	A, di/dt = 100 A/µs	-	15	-	ns	
Reverse recovery rise time	t _b	1		-	4	-		
Body diode peak reverse recovery current	I _{RM(REC)}	1		-	-2.1	-	Α	

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$

b. Guaranteed by design, not subject to production testing

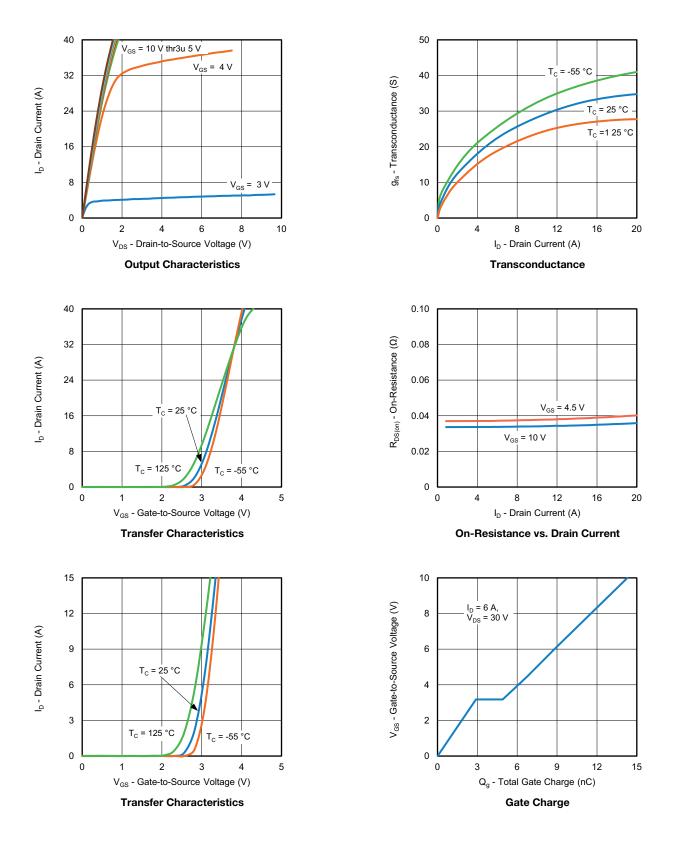
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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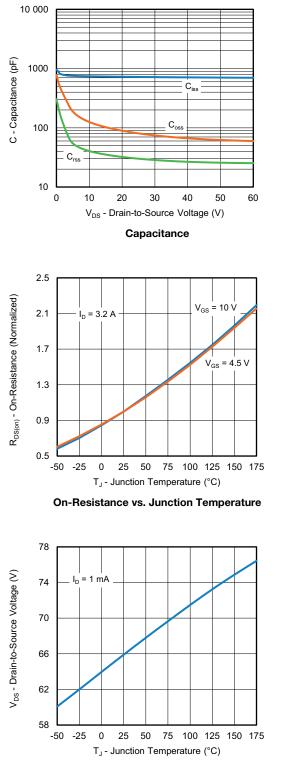
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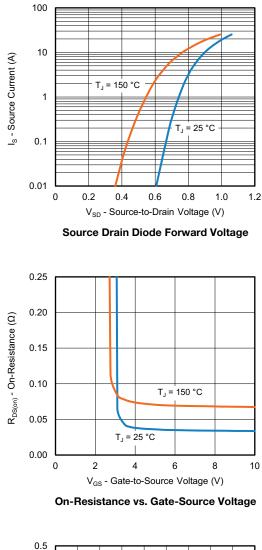
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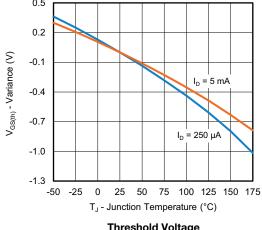
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Drain Source Breakdown vs. Junction Temperature





Threshold Voltage

4

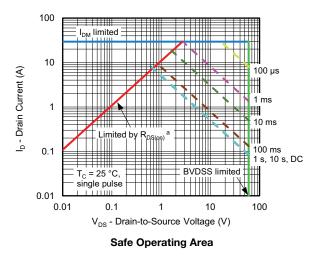
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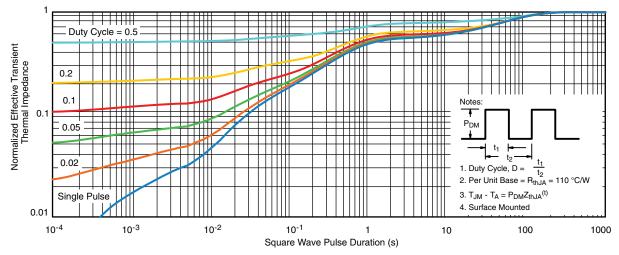
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Ambient

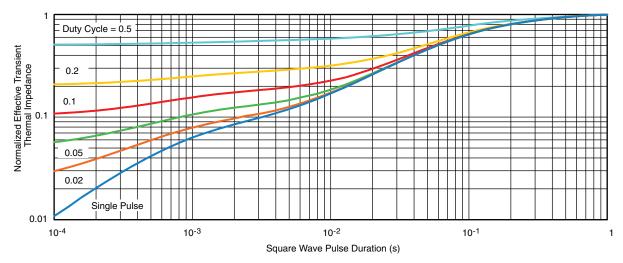




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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62059.



Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



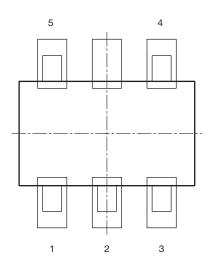
	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
Е	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е		0.95 BSC		0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁		0.60 Ref		0.024 Ref		
L ₂	0.25 BSC				0.010 BSC	
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom				7° Nom	
ECN: C DWG: 5		ev. I, 18-Dec	c-06			

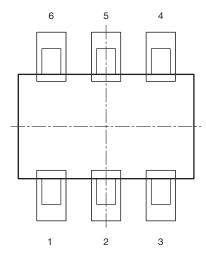
PAD Pattern



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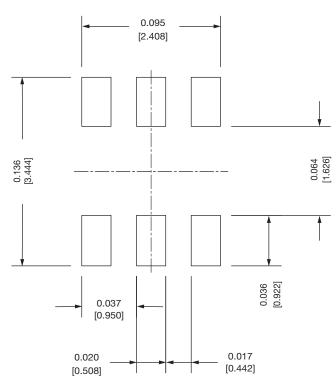
Recommended Land Pattern For TSOP-5L / TSOP-6L





TSOP 5L





Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022	
DWG: 3010	



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